■ Job Information

Subject No.	2020R-2
Job Title	Fixed Term Researcher
Department	Advanced ICT Research Institute / Green ICT Device Advanced Development Center
Work Contents (Research theme)	Research and development on gallium oxide devices (device processing)
Detail of Work Contents	Research and development on fundamental technologies for electrical devices based on novel widegap semiconductor; gallium oxide (Ga2O3). The successful candidates will be in charge of Ga2O3 device processing. The Article 15(2) of the Act on the activation of Science and Technology and Innovation will be applied to this work content.
Application requirement	Ph.D. or equivalent in Electrical Engineering or a related discipline, with 5+ years of industry experience (R&D and production). Minimum 3 years of R&D hands-on experiences in semiconductor electrical device processing and characterization. Special consideration will be given to candidates with expertise and experience in device fabrication process and characterization based on widegap, compound semiconductor materials (GaN, SiC, GaAs etc).
Recruiting (Number of people)	1
Period of Employment	hiring date 〜 March 31,2021 N.B. Contract will not be renewed..
Salary (basic salary)	¥467,000 〜 ¥510,000／month Basic salary shall be determined by taking into account each employee’s experience and task to be engaged in. However, as a basic salary is compliant with government employees' wages, it shall be changed when a basic salary is changed after labor union and the like of NICT agreed under a revision to the government employees' wages.
Work Place	Headquarters (Koganei-shi, Tokyo)
Working frequency	5days/week（7.5hours/day）

Department name and work place including work contents (research theme) and detail of work contents might change according to organizational change, etc.